

P-Channel NexFET™ Power MOSFETs

Check for Samples: [CSD25401Q3](#)

FEATURES

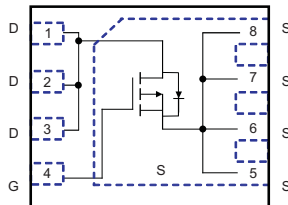
- Ultra Low Q_g and Q_{gd}
- Low Thermal Resistance
- Low $R_{DS(on)}$
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 3.3mm x 3.3mm Plastic Package

APPLICATIONS

- DC-DC Converters
- Battery Management
- Load Switch
- Battery Protection

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion load management applications. The SON 3x3 package offers excellent thermal performance for the size of the package.

Top View

Table 1. PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	-20	V
Q_g	Gate Charge Total (4.5V)	8.8	nC
Q_{gd}	Gate Charge Gate to Drain	2.1	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = -2.5V$	13.5 mΩ
		$V_{GS} = -4.5V$	8.8 mΩ
V_{th}	Threshold Voltage	-0.85	V

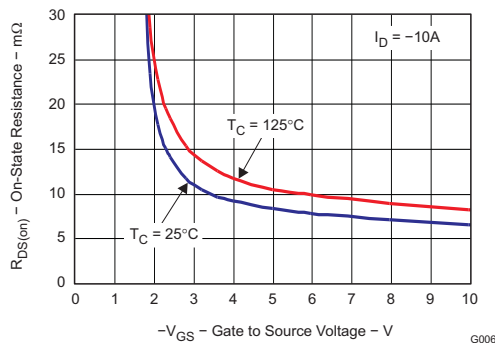
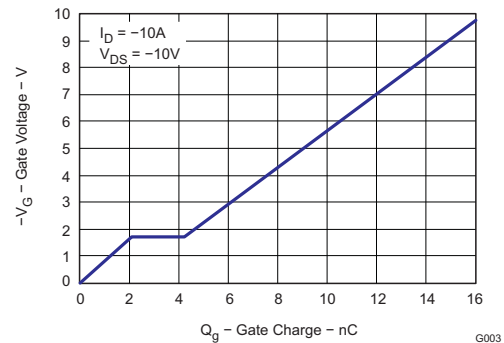
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD25401Q3	SON 3 x 3 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	+12 / -12	V
I_D	Continuous Drain Current, $T_C = 25^\circ\text{C}$	-60	A
	Continuous Drain Current ⁽¹⁾	-14	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ ⁽²⁾	-82	A
P_D	Power Dissipation ⁽¹⁾	2.8	W
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

- (1) $R_{\theta JA} = 45^\circ\text{C/W}$ on 1inch² Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

 $R_{DS(on)}$ vs V_{GS}

Gate Charge


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ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
B _V DSS	Drain to Source Voltage	V _{GS} = 0V, I _D = -250μA	-20			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = -20V to -16V			-1	μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = ±12V			-100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.6	-0.85	-1.2	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = -2.5V, I _D = -10A		13.5	18.2	mΩ
		V _{GS} = -4.5V, I _D = -10A		8.8	11.7	mΩ
g _{fs}	Transconductance	V _{DS} = -15V, I _D = -10A		43		S
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V, V _{DS} = -10V, f = 1MHz		1070	1400	pF
C _{OSS}	Output Capacitance			560	730	pF
C _{RSS}	Reverse Transfer Capacitance			180	230	pF
Q _g	Gate Charge Total (4.5V)	V _{DS} = -10V, I _D = -10A		8.8	12.3	nC
Q _{gd}	Gate Charge Gate to Drain			2.1		nC
Q _{gs}	Gate Charge Gate to Source			2.1		nC
Q _{g(th)}	Gate Charge at V _{th}			0.9		nC
Q _{OSS}	Output Charge		V _{DS} = -10V, V _{GS} = 0V		8.2	
t _{d(on)}	Turn On Delay Time	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -10A, R _G = 5.1Ω		8.1		ns
t _r	Rise Time			3.9		ns
t _{d(off)}	Turn Off Delay Time			13.5		ns
t _f	Fall Time			12.6		ns
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _S = -10A, V _{GS} = 0V		-0.7	-1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = -12.5V, I _F = -10A, di/dt = 300A/μs		17.4		nC
t _{rr}	Reverse Recovery Time			21		ns

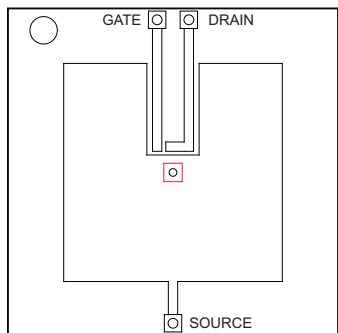
THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
R _{θJC}	Thermal Resistance Junction to Case ⁽¹⁾ ⁽²⁾			2.8	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ ⁽²⁾			57	°C/W

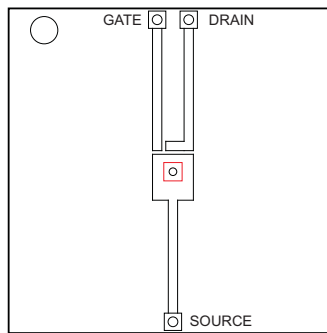
(1) R_{θJC} is determined with the device mounted on a 1 inch² Cu (2 oz.) pad on a 1.5 × 1.5 in 0.060 inch thick FR4 board. R_{θJC} is specified by design while R_{θJA} is determined by the user's board design.

(2) Device mounted on FR4 Material with 1 inch² of Cu (2 oz.).



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Max $R_{\theta JA} = 57^{\circ}\text{C/W}$
when mounted on
 1inch^2 of 2 oz. Cu.

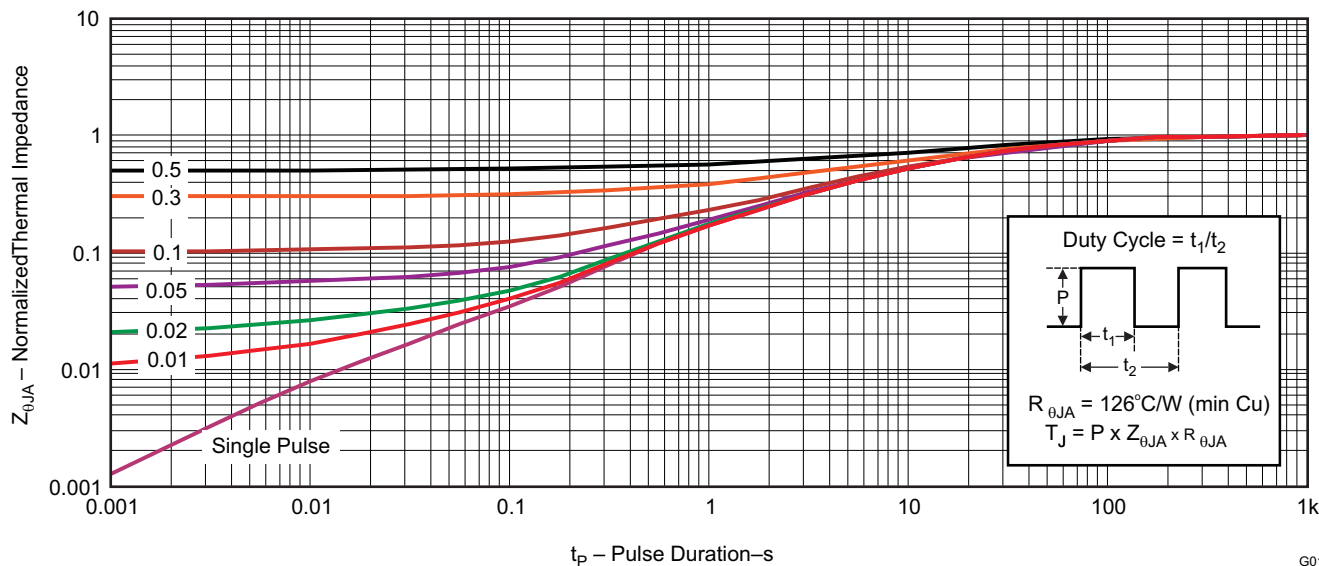


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Max $R_{\theta JA} = 158^{\circ}\text{C/W}$
when mounted on
minimum pad area of 2
oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)



G012

Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

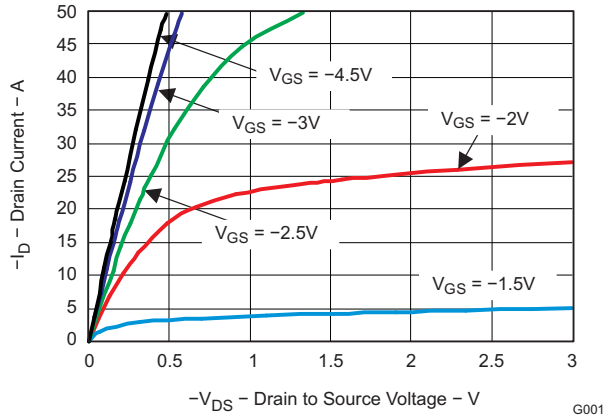


Figure 2. Saturation Characteristics

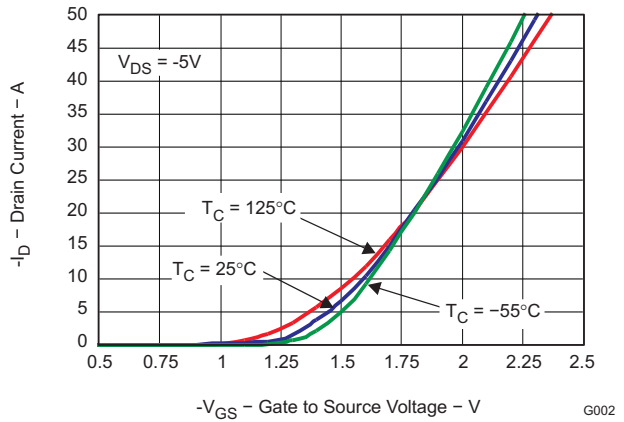


Figure 3. Transfer Characteristics

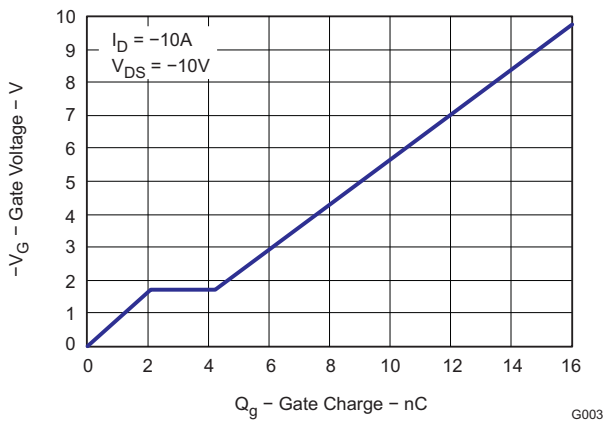


Figure 4. Gate Charge

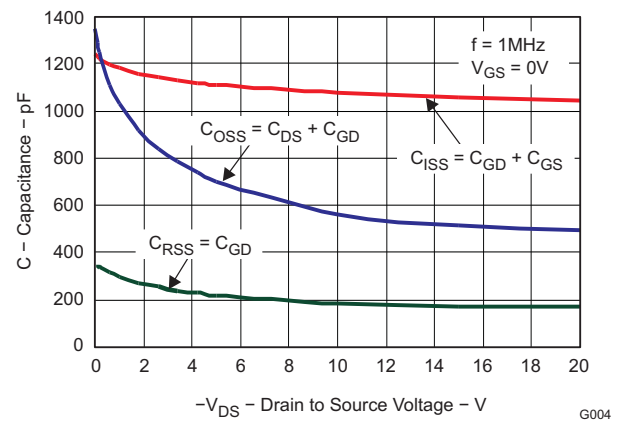


Figure 5. Capacitance

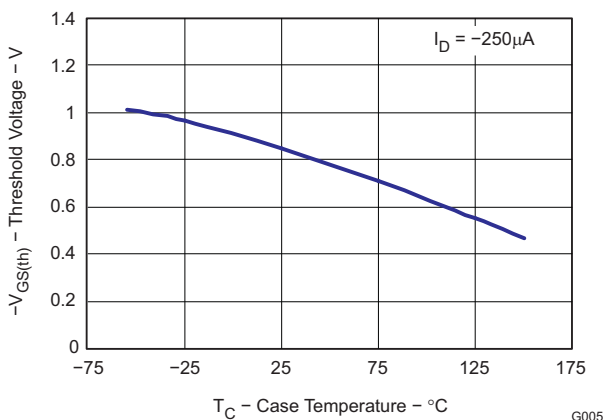


Figure 6. Threshold Voltage vs. Temperature

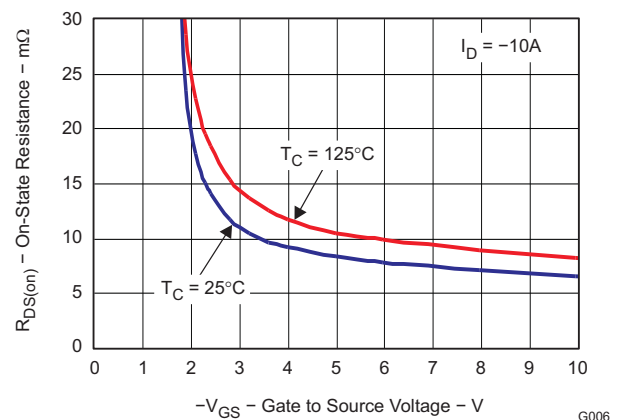


Figure 7. On Resistance vs. Gate Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

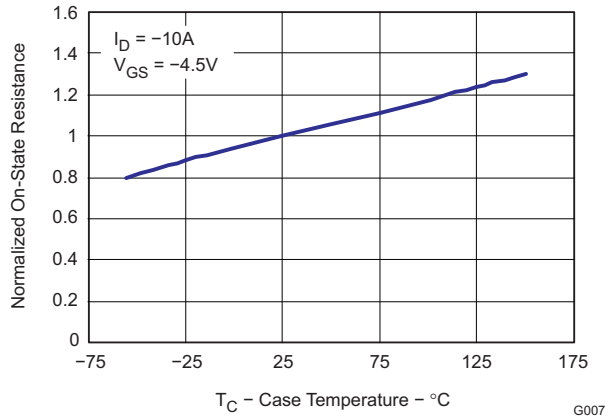


Figure 8. On Resistance vs. Temperature

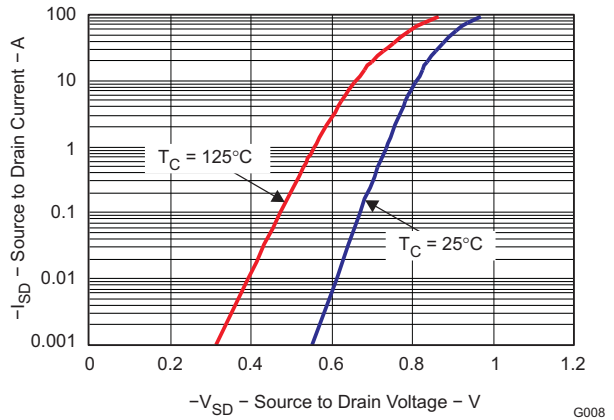


Figure 9. Typical Diode Forward Voltage

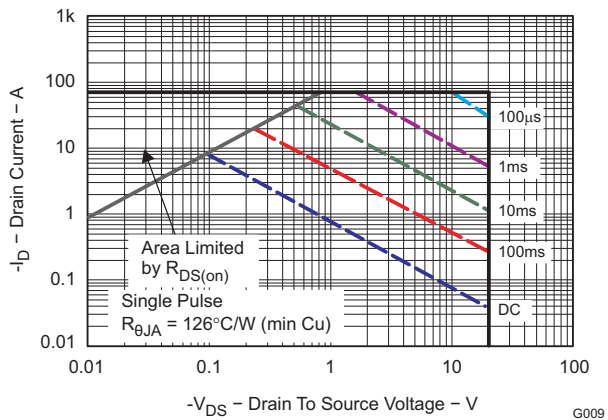


Figure 10. Maximum Safe Operating Area

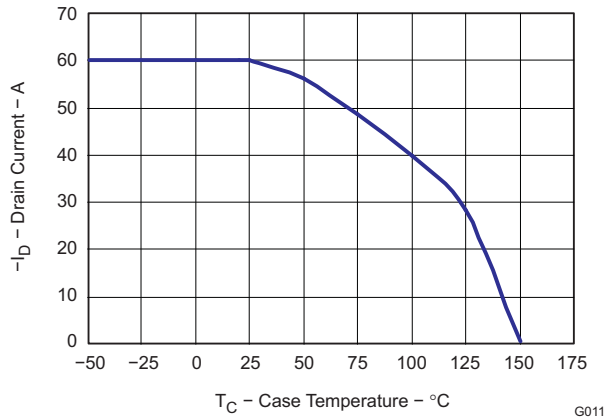
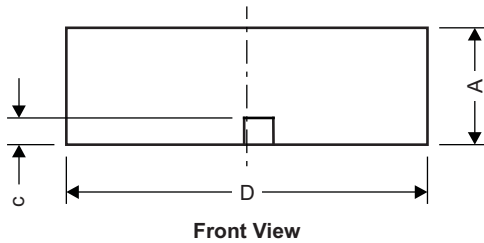
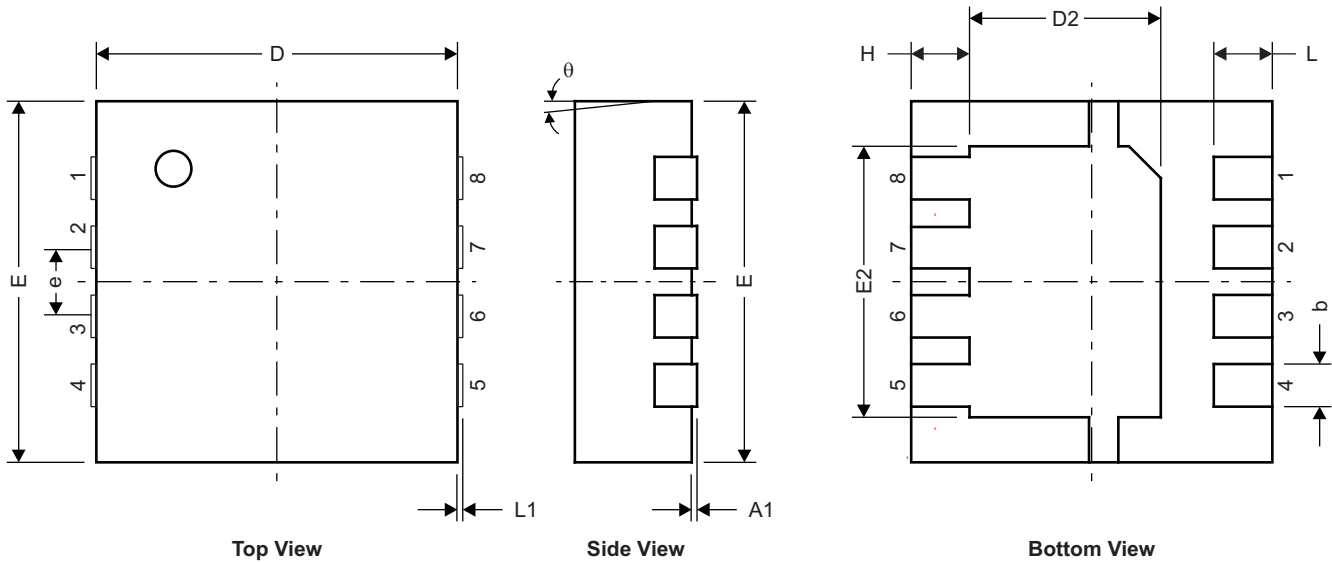


Figure 11. Maximum Drain Current vs. Temperature

MECHANICAL DATA

CSD25401Q3 Package Dimensions



Pinout	
Drain	1,2,3
Gate	4
Source	5,6,7,8

M0142-01

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D1	-	-	-	-	-	-
D2	1.650	1.750	1.800	0.065	0.069	0.071
E	3.200	3.300	3.400	0.126	0.130	0.134
E1	-	-	-	-	-	-
E2	2.350	2.450	2.550	0.093	0.096	0.100
e	0.650 TYP			0.026		
H	0.35	0.450	0.550	0.014	0.018	0.022
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	-	-	-	-	-	-
θ	-	-	-	-	-	-

REVISION HISTORY

Changes from Original (August 2009) to Revision A **Page**

- Changed 300s to 300 μ s in Note 2 of the Abs Max Ratings table 1
 - Changed Q_g Gate Charge Total (4.5V) - max value From: 2.3 To: 12.3 2
-

Changes from Revision A (October 2009) to Revision B **Page**

- Deleted the Package Marking Information section 7
-

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25401Q3	SON	DQG	8	2500	330.0	12.8	3.6	3.6	1.2	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD25401Q3	SON	DQG	8	2500	335.0	335.0	32.0

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